

Silence of magnetic layers to magnetoresistive process and electronic separation at low temperatures in (La, Sm)Mn₂Ge₂

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Abstract

A closer look at the temperature (T) dependence of magnetoresistance (MR) of two polycrystalline magnetic compounds, LaMn₂Ge₂ and SmMn₂Ge₂, previously reported by us, is made. A common feature for both these compounds is that the low temperature MR is positive (say, below, 30 K) in spite of the fact that both are ferromagnetic at such low temperatures; in addition, MR as a function of magnetic field (H) does not track magnetization (M) in the sense that M saturates at low fields, while MR varies linearly with H. These observations suggest that the magnetic layers interestingly do not dominate low temperature magnetotransport process. Interestingly enough, as the T is increased, say around 100 K, these magnetic layers dominate MR process as evidenced by the tracking of M and MR in SmMn₂Ge₂. These results tempts us to propose that there is an unusual "electronic separation" for MR process as the T is lowered in this class of compounds.

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The understanding of electrical resistance (R) behaviour in solids continues to be a major direction of research in condensed matter physics. In general, in metals containing magnetic impurities or a large concentration of magnetic-moment-carrying ions, one observes a dominant signature of these magnetic ions in the *low temperature* (T) electrical resistance, which has a characteristic response with the application of an external magnetic field (H)¹ depending upon the magnetic state. For instance, in ferromagnetic materials R decreases with increasing H; Y (non-magnetic), if contains Ce in traces, exhibits features due to the Kondo effect resulting in a decrease of R with H². Here we argue that, in sharp contrast to this expectation, in a class of layered ternary intermetallic compounds containing a magnetically ordered layer, viz., RMn₂Ge₂ (R= La, Sm), the non-magnetic atomic layers dominate the magnetoresistance (MR) at low temperatures with the magnetic layers apparently remaining "silent"; however, with increasing temperature, the contribution from the magnetic atomic layers is visible. This is taken as an evidence to suggest that there is a temperature dependence associated for the involvement of different layers; in other words apparently there is "an electronic separation" with decreasing temperature for the magnetoresistive process. This finding adds a new dimension to the understanding of magnetotransport phenomena in solids.

The intermetallic compounds under discussion crystallize in the well-known ThCr₂Si₂-

type tetragonal structure³, containing layers of atoms stacked in the sequence Th-Si-Cr-Si-Th along the c-axis. It is interesting to note that, among few hundred compounds known to form in this structure, the Mn is the only transition metal ion known to possess magnetic moment and magnetic ordering at very high temperatures. The nature of the magnetic ordering apparently is sensitive to Mn-Mn distances and this appears to explain the presence of multiple magnetic transitions for Sm compound with the Mn-Mn distance for this compound falling near the critical limit [3]. Thus, while the former compound has been known to order ferromagnetically at about 300 K with the magnetism arising from Mn sublattice, the latter exhibits multiple magnetic transitions: below about 345 K, para- to ferro-magnetism; at about 140 K, ferro to anti-ferromagnetism; and antiferro to ferromagnetism below about 105 K (see, for instance, Refs. 3-13). It is surprising to note that, inspite of extensive magnetic investigations on this class of ternary compounds, virtually there has been very little MR studies on these Mn alloys. Though the compound SmMn_2Ge_2 was investigated in the range 80 - 150 K to show giant magnetoresistance effects earlier^{6,7}, surprisingly these authors did not report the MR at lower temperatures. Considering a recent upsurge in MR studies in condensed matter physics, we considered it important to carry out such studies on these compounds and thus we reported the MR alongwith detailed magnetic measurements down to 4.2 K⁹⁻¹²; the major point of emphasis was to bring out the relevance of these compounds to the physics of artificial multilayers. In this letter, for the La and Sm compounds, we take into account available data in the literature and also compare the T dependence of MR to draw the present conclusion. As far as our data is concerned, we reproduce here only those data which are required to emphasize this point.

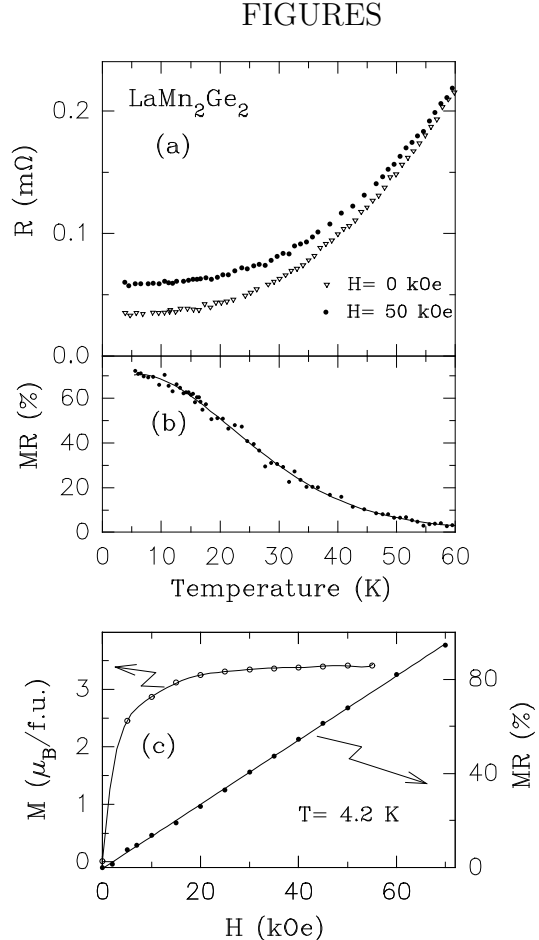


FIG. 1. Electrical resistance (R) and magnetization behaviour of LaMn_2Ge_2 : **(a)** The R data in zero field and in the presence of 50 kOe; **(b)** The derived magnetoresistance ($\text{MR} = [R(H) - R(0)]/R(0)$) as a function of temperature (4.2-60 K). The typical isothermal magnetization data and MR as a function of externally applied magnetic field in the ferromagnetically ordered state, say at 4.2 K, are shown in **(c)**. The lines through the data points are guides to the eyes.

In figure 1a, we show R as a function of T in zero field as well as at 50 kOe (with the direction of H being parallel to that of the excitation current) for a specimen of LaMn_2Ge_2 below 60 K. The magnetoresistance [$\text{MR} = \{R(H) - R(0)\}/R(0)$] behaviour, obtained by subtracting the zero-field R data from that at 50 kOe is shown in figure 1b. The value of MR increases with

decreasing temperature below 60 K eventually attaining large values at 4.2 K; at temperatures higher than 60 K the value of MR is negligibly small. *What is intriguing is that the sign of MR is positive at low temperatures*, inspite of the fact that the compound contains ferromagnetic Mn layers in which case one should have observed MR with a negative sign expected for polycrystalline ferromagnetic metals¹. (Therefore, it is the ferromagnetic nature of the magnetic ordering that enables us to draw the present conclusions on firm grounds, as positive MR for antiferromagnetics is usually expected.) We have obtained MR on several specimens of this compound prepared under different conditions of heat-treatment and the positive sign of MR is always reproducible^{11,12}. The

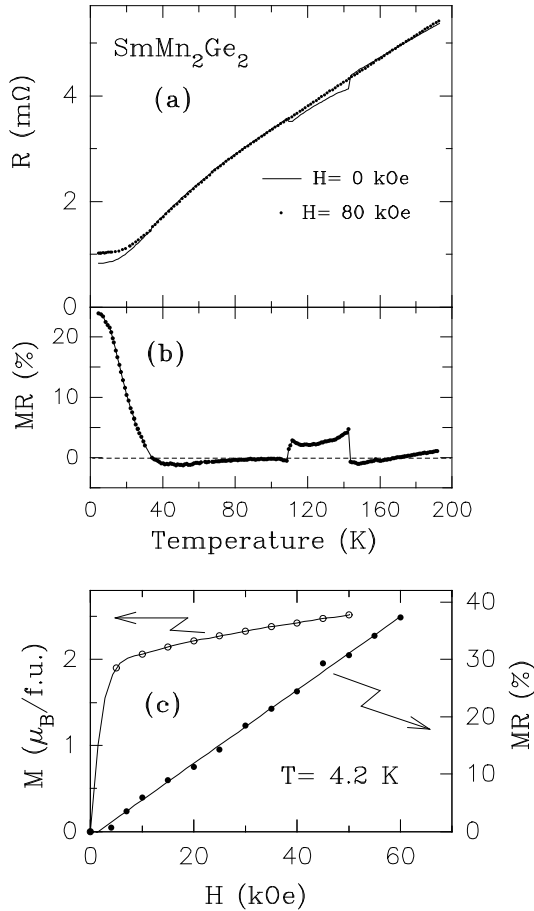


FIG. 2. Electrical resistance (R) and magnetization behaviour of $SmMn_2Ge_2$: (a) The R in the presence and in the absence of magnetic field (50 kOe) as a function of temperature. The magnetoresistance derived from this data are plotted in (b). The isothermal magnetization data and MR as a function of externally applied magnetic field at 4.2 K are shown in (c) and the lines through the data points are guides to the eyes.

positive sign of MR is taken as an evidence for the dominant role of non-magnetic layers in controlling magnetoresistive process. Needless to mention that the positive sign of MR is characteristic of non-magnetic metals. Even if one attributes positive sign of MR to possible deviations⁵ from collinear ferromagnetism of the Mn sublattice or to any other mechanism arising from ferromagnetism, the following finding goes against these possibilities. That is, the magnetization does not track MR (e.g., at 4.2 K, see Fig. 1c) in the sense that M saturates for small applications of H while MR is a linearly varying function of H . This is a *key finding* in favour of our proposal that in this compound the Mn magnetic layer is not apparently involved in the magnetotransport phenomena at low temperatures. In metallic materials, at low temperatures, the disorder/impurity scattering contribution dominates as the phonon contribution tends to vanish. Therefore, one may advance an argument that the positive sign of MR somehow arises from such crystallographic imperfections. However, a careful look at how MR varies as a function of the residual resistivity ratio, $RRR [= R(4.2K)/R(300K)]$, in specimens with different degree of crystallographic imperfections¹² clearly reveals that the increasing disorder/imperfections in fact tend to *diminish* the net change in R by the application of H at low T . This naturally implies that the observed positive sign with a large magnitude is intrinsic to the crystallographically well-ordered material. We therefore

conclude that the positive MR arises from La and/or Ge layer only, without involving magnetic-moment-carrying Mn ions.

The present conclusion is novel as it has been generally believed that the signature of moment-carrying ions should be prominent in the low temperature transport behaviour; this contribution can be so prominent that even in the dilute limit of 3d magnetic impurities in non-magnetic matrices one usually encounters the phenomenon of the Kondo effect^{2,14} with corresponding magnetoresistive response. [It may be added that the temperature dependence of mean free path (mfp) also seems to correlate with MR¹². In spite of the fact that there are uncertainties in the absolute values of mfp due to approximations in its determination, it appears that the critical value for the observation of significant positive MR is of the order of interlayer spacings. We believe that this information may be useful for future theoretical work.]

Next, one might be tempted to ask the following questions. Which of the two layers, La or Ge, dominates low temperature scattering phenomenon? Do magnetic layers participate in magnetotransport phenomena as the temperature is increased? The transport behaviour of SmMn_2Ge_2 offers straightforward answers for these questions. The data are shown in Fig. 2a in zero and 50 kOe field. MR is distinctly positive at low temperatures even in this compound, without tracking isothermal M (see Fig. 2c), the origin of which must be the same as that in the La compound.³ However, as the temperature is increased, as known earlier³, the jumps in R in zero field at about 110 K and 140 K attributable to magnetic transitions arising from Mn are clearly seen. The application of H wipes out these jumps due to the well-known^{3,6} sharp metamagnetic transition occurring at about 5 kOe, thus resulting in large MR anomalies at these temperatures (Fig. 2b). Thus, it is evident that the Mn

(magnetic) layer gets involved in the transport process at these temperatures. This conclusion is further endorsed by the observation^{6,7} that *MR tracks magnetization as a function of H at 104 K, unlike the situation at 4.2 K*. In fact, the expected negative sign of MR starts appearing as the temperature is increased beyond 30 K, thereby indicating that the (ferro)magnetic layer dominates above this temperature in this compound. It is also important to note that Sm layer also orders ferromagnetically³ below 100 K and if this layer dominates low temperature (< 30 K) MR, one should have seen negative MR tracking isothermal M, in sharp contrast to the experimental observations. This establishes that it is not even the rare-earth layer, but the Ge layer, that dominates low temperature magnetotransport phenomena.

Summarising, a comparison of MR behaviour of the compounds LaMn_2Ge_2 and SmMn_2Ge_2 suggests that the dominance of magnetic layers to the magnetotransport process diminishes with decreasing temperature, meaning thereby that there is an unusual temperature dependence associated with the relative involvement of layers of atoms for this process. Thus there appears to be an interesting "electronic separation" at the unit-cell level as the temperature is lowered as far as the magnetotransport is concerned. The above suggestion is made under the assumption that there are no unusual band structure effect on MR (which, if present, is by itself again interesting); the presently available band structure data³ do not reveal any unusual structure at the Fermi level within the energy scale of the magnitude of applied magnetic field and hence we advance the present line of thoughts. At this point, it is worth mentioning that, at the time of finalising this article, the idea of an electronic phase separation at a length scale much larger than the unit-cell dimensions has been proposed to explain the colossal magnetoresistance in

mixed-valent manganites¹⁵. It is fascinating that some kind of electronic separation (as far as magnetoresistance is concerned) may be possible with the variation of temperature *even at the unit-cell level* as indicated by the present data. Realisation of this possibility will go a long way in understanding the transport process in modern condensed matter physics.

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